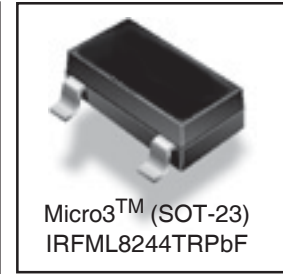
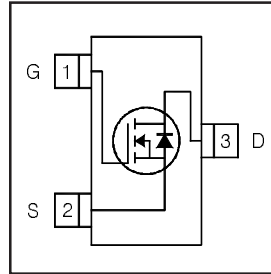


IRFML8244TRPbF

HEXFET® Power MOSFET



V_{DS}	25	V
$V_{GS\ Max}$	± 20	V
$R_{DS(on)\ max}$ (@ $V_{GS} = 10V$)	24	m Ω
$R_{DS(on)\ max}$ (@ $V_{GS} = 4.5V$)	41	m Ω



Application(s)

- Load/ System Switch

Features and Benefits

Features

Low $R_{DS(on)}$ ($\leq 24m\Omega$)
Industry-standard pinout
Compatible with existing Surface Mount Techniques
RoHS compliant containing no lead, no bromide and no halogen
MSL1, Consumer qualification

results in
 $\Rightarrow$

Benefits

Lower switching losses
Multi-vendor compatibility
Easier manufacturing
Environmentally friendly
Increased reliability

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	25	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.8	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.6	
I_{DM}	Pulsed Drain Current	24	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation	1.25	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation	0.80	
	Linear Derating Factor	0.01	
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	—	100	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient (t<10s) ④	—	99	

Electric Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	25	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	20	24	$m\Omega$	$V_{GS} = 10V, I_D = 5.8A$ ②
		—	32	41		$V_{GS} = 4.5V, I_D = 4.6A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.7	2.35	V	$V_{DS} = V_{GS}, I_D = 10\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
R_G	Internal Gate Resistance	—	1.6	—	Ω	
g_{fs}	Forward Transconductance	10	—	—	S	$V_{DS} = 10V, I_D = 5.8A$
Q_g	Total Gate Charge	—	5.4	—	nC	$I_D = 5.8A$
Q_{gs}	Gate-to-Source Charge	—	1.0	—		$V_{DS} = 13V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	0.81	—		$V_{GS} = 10V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	2.7	—	ns	$V_{DD} = 13V$ ②
t_r	Rise Time	—	2.1	—		$I_D = 1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	9.0	—		$R_G = 6.8\Omega$
t_f	Fall Time	—	2.9	—		$V_{GS} = 10V$
C_{iss}	Input Capacitance	—	430	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	110	—		$V_{DS} = 10V$
C_{rss}	Reverse Transfer Capacitance	—	49	—		$f = 1.0\text{MHz}$

Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.25	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	24		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 5.8A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	11	17	ns	$T_J = 25^\circ\text{C}, V_R = 20V, I_F = 5.8A$
Q_{rr}	Reverse Recovery Charge	—	4.2	6.3	nC	$di/dt = 100A/\mu s$ ②

